

**IN THE SPECIFICATION:**

The specification as amended below with replacement paragraphs shows added text with underlining and deleted text with ~~striketrough~~.

Please REPLACE paragraph [0012], with the following paragraph:

**[0012]** An ~~Axelis-GSD~~Axcelis GSD<sup>TM</sup> platform implanter may be used to implant ions in the first and second wafers. The following equation may be used to estimate the rate at which neutral ions are implanted:

$$I_{\text{MEASURED}} = I_{\text{DOSE}} \cdot e^{-kp}$$

where  $I_{\text{MEASURED}}$  is the rate at which ions are implanted,  $I_{\text{DOSE}}$  is the sum of the rate at which ions are implanted and the estimated rate at which neutral atoms are implanted, K is a pressure compensation factor and P is the pressure. A parameter P-COMP relates to the pressure compensation factor K according to the following equation:

$$K = \ln\left(1 + \frac{P - \text{COMP}}{100}\right)(10000) .$$